

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	41708	(gallium adj nitride) or GaN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/25 12:02
L2	11841	L1 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/25 12:02
L3	259	L2 and (atomic adj nitrogen or nitriding)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/25 12:02
L4	991	(438/194,285,574,767,775,777). CCLS.	US-PGPUB; USPAT	OR	OFF	2006/07/25 13:43
L5	0	(gallium nitride or GaN) and (aluminum layer) and (atomic nitrogen) and (catalytic member) and gate and source and drain	US-PGPUB; USPAT	ADJ	ON	2006/07/25 13:47